NSN 5962-01-444-6546

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Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

F-15i

Features Provided:

Electrostatic sensitive and monolithic and static operation

Inclosure Material:

Silicon

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Criticality Code Justification:

Cbbl

Current Rating Per Characteristic:

15.00 milliamperes forward current, peak total value not applicable

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, memory, digital, cmos, 2k x 8 non-volatile static ram, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.6 volts total supply and 7.0 volts total supply

Time Rating Per Chacteristic:

55.00 nanoseconds access

Memory Device Type:

Ram

Special Features:

Descriptive designator cdip3-t28 or gdip4-t28; circuit function 8k x 8 nvsram

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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